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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/596,359	06/09/2006	Hajime Kando	36856.1450	5636
54066 7590 07/11/2008 MURATA MANUFACTURING COMPANY, LTD. C/O KEATING & BENNETT, LLP 1800 Alexander Bell Drive SUITE 200 Reston, VA 20191				
			EXAMINER ROSENAU, DEREK JOHN	
			ART UNIT 2834	PAPER NUMBER
			NOTIFICATION DATE 07/11/2008	DELIVERY MODE ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

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Office Action Summary

Application No.

10/596,359

Applicant(s)

KANDO, HAJIME

Examiner

Derek J. Rosenau

Art Unit

2834

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 24 April 2008.
2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 23-42 is/are pending in the application.
4a) Of the above claim(s) _____ is/are withdrawn from consideration.
5) ☐ Claim(s) _____ is/are allowed.
6) ☒ Claim(s) 23-42 is/are rejected.
7) ☐ Claim(s) _____ is/are objected to.
8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☒ The specification is objected to by the Examiner.
10) ☒ The drawing(s) filed on 24 April 2008 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☒ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☒ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☒ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☐ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☐ Information Disclosure Statement(s) (PTO-8508)
4) ☐ Interview Summary (PTO-413)
5) ☐ Notice of Informal Patent Application
6) ☐ Other: _____
Paper No(s)/Mail Date _____

DETAILED ACTION

Drawings

1. The drawings were received on 24 April 2008. These drawings are accepted.

Specification

2. Applicant is reminded of the proper language and format for an abstract of the disclosure.

The abstract should be in narrative form and generally limited to a single paragraph on a separate sheet within the range of 50 to 150 words. It is important that the abstract not exceed 150 words in length since the space provided for the abstract on the computer tape used by the printer is limited. The form and legal phraseology often used in patent claims, such as "means" and "said," should be avoided. The abstract should describe the disclosure sufficiently to assist readers in deciding whether there is a need for consulting the full patent text for details.

The language should be clear and concise and should not repeat information given in the title. It should avoid using phrases which can be implied, such as, "The disclosure concerns," "The disclosure defined by this invention," "The disclosure describes," etc.

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

4. Claims 23-29, 31, 33, and 35 are rejected under 35 U.S.C. 103(a) as being unpatentable over Itakura et al. (US 2002/0158549) in view of Taniguchi (US 2001/0008387) and Takayama et al. (US 20040174233).
5. With respect to claim 29, Itakura et al. discloses a boundary acoustic wave device (Fig 1) using a non-leaky propagation type boundary acoustic wave, comprising:

a boundary acoustic wave element, including a single crystal substrate (item 4), a solid layer (item 6) provided on the single crystal substrate, and electrodes (item 5) arranged at a boundary between the single crystal substrate and the solid layer (Fig 1); wherein the single crystal substrate has a cut angle (Paragraph 86).

Itakura et al. does not disclose expressly a plurality of boundary acoustic wave elements, the single crystal substrates of those elements having the same cut angle, or a propagation direction of a boundary acoustic wave of at least one of the boundary acoustic wave elements is different from that of at least one of the other boundary acoustic wave resonators, or that the thickness of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate.

Taniguchi teaches a boundary acoustic wave device having a plurality of boundary acoustic wave elements (Fig 5), the single crystal substrates of those elements having the same cut angle (Paragraph 49), and a propagation direction of a boundary acoustic wave of at least one of the boundary acoustic wave elements is different from that of at least one of the other boundary acoustic wave resonators (Fig 5).

Takayama et al. teaches a boundary acoustic wave device in which the thickness of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through

the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate (Paragraphs 8 and 83). Although Takayama et al. does not disclose explicitly the functional language "so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate," this would be inherent as Takayama et al. discloses the electrode thicknesses disclosed in the specification.

At the time of invention, it would have been obvious to a person of ordinary skill in the art to combine the plurality of boundary acoustic wave elements having different propagation directions of Taniguchi and the electrode thickness of Takayama et al. with the boundary acoustic wave device of Itakura et al. for the benefit of allowing for different electromechanical coupling coefficients within the same device (Paragraph 58 of Taniguchi) and of reducing the propagation loss (Paragraph 8 of Takayama et al.).

6. With respect to claim 23, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29. Taniguchi discloses that the plurality of boundary acoustic wave elements are boundary acoustic wave filters or boundary acoustic wave resonators (Paragraph 58).
7. With respect to claim 24, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29. Taniguchi discloses that the plurality of boundary acoustic wave elements define resonators (Paragraph 58).

8. With respect to claim 25, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29. Taniguchi discloses that the boundary acoustic wave device is a longitudinally coupled filter (Fig 5).
9. With respect to claim 26, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29. Taniguchi discloses that the boundary acoustic wave elements are provided on a single piezoelectric single crystal substrate (Paragraph 58).
10. With respect to claim 27, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29. Taniguchi discloses that an electromechanical coefficient of at least one of the boundary acoustic wave elements is different from that of at least one of the other boundary acoustic wave elements (Paragraph 58).
11. With respect to claim 28, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29. Taniguchi discloses that a band width of at least one of the boundary acoustic wave elements is different from that of at least one of the other boundary acoustic wave elements (Paragraph 55).
12. With respect to claim 31, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29. Taniguchi discloses that $H > 8261.744\rho^{-1.376}$, when ρ represents the density of the electrodes, H represents the thickness of the electrodes, and λ represents the

wavelength of a boundary wave. The claim language does not define the wavelength or how to determine it; therefore, the wavelength can be any desired value. Therefore, the electrode thickness would meet the condition $H > 8261.744p^{-1.376}$ for some value of λ .

13. With respect to claim 33, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 31. Taniguchi discloses that $33000.39050p^{-1.50232} < H < 88818p^{-1.54998}$. The claim language does not define the wavelength or how to determine it; therefore, the wavelength can be any desired value. Therefore, the electrode thickness would meet the condition $33000.39050p^{-1.50232} < H < 88818p^{-1.54998}$ for some value of λ .

14. With respect to claim 35, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29. Taniguchi discloses that the electrodes each include a main electrode layer made from a material selected from the group consisting of Au, Ag, Cu, Al, Fe, Ni, W, Ta, Pt, Mo, Cr, Ti, ZnO, and ITO (Paragraph 61).

15. Claim 30 is rejected under 35 U.S.C. 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., and Takamine (US 20020135267).

16. With respect to claim 30, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29.

None of Itakura et al., Taniguchi, or Takayama et al. discloses expressly that a duty ratio of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating

through the solid layer and the acoustic velocity of a slow transverse layer propagating through the piezoelectric single crystal substrate.

Takamine teaches a boundary acoustic wave device in which a duty ratio of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse layer propagating through the piezoelectric single crystal substrate (Paragraph 64 and Table 1). Although Takamine does not disclose explicitly the functional language "so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the solid layer and the acoustic velocity of a slow transverse layer propagating through the piezoelectric single crystal substrate," this would be inherent as Takamine discloses the IDT duty ratios disclosed in the specification.

At the time of invention, it would have been obvious to a person of ordinary skill in the art to combine the IDT duty ratio of Takamine with the boundary acoustic wave device of Itakura et al. as modified by Taniguchi and Takayama et al. as it has been held that optimization of a device, where the general conditions are met by the prior art, would be obvious to a person of ordinary skill in the art (*In re Aller*, 105 USPQ 233).

17. Claim 34 is rejected under 35 U.S.C. 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., and Nakahata (US 6025636).

18. With respect to claim 34, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29.

None of Itakura et al., Taniguchi, or Takayama et al. discloses that the piezoelectric single crystal substrate is LiNbO_3 substrate, ϕ of Euler angles (ϕ, θ, ψ) of the LiNbO_3 substrate is in the range -31° to 31° , and θ and ψ are in the range surrounded by the points A1 to A13 shown in table 1

Points	$\Psi(^{\circ})$	$\Theta(^{\circ})$
A01	0	116
A02	11	118
A03	20	123
A04	25	127
A05	33	140
A06	60	140
A07	65	132
A08	54	112
A09	48	90
A10	43	87
A11	24	90
A12	0	91
A13	0	118

Nakahata teaches a boundary acoustic wave device in which the piezoelectric single crystal substrate is LiNbO_3 substrate, ϕ of Euler angles (ϕ, θ, ψ) of the LiNbO_3

substrate is in the range -31° to 31° , and θ and ψ are in the range surrounded by the points A1 to A13 (column 9, line 65 through column 10, line 18).

At the time of invention, it would have been obvious to a person of ordinary skill in the art to combine the crystal orientation of Nakahata with the boundary acoustic wave device of Itakura et al. as modified by Taniguchi and Takayama et al. for the benefit of an acoustic velocity of 8000 m/s or higher (column 10, lines 34-42).

19. Claims 32, 36-38, and 41 are rejected under 35 U.S.C. 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., and Nishiyama et al. (US 2007/0132339).

20. With respect to claim 32, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 31.

None of Itakura et al., Taniguchi, or Takayama et al. disclose that $\rho > 3745 \text{ kg/m}^3$.

Nishiyama et al. teaches a boundary acoustic wave device in which the electrode may be made of a large number of materials, among them materials having densities greater than 3745 Kg/m^3 (Paragraph 32).

At the time of invention, it would have been obvious to a person of ordinary skill in the art to combine the electrode materials of Nishiyama et al. with the boundary acoustic wave device of Itakura et al. as modified by Taniguchi and Takayama et al. as the electrode materials taught by Nishiyama are well known for their use as electrode materials.

21. With respect to claim 36, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 35.

None of Itakura et al., Taniguchi, or Takayama et al. discloses that the electrodes each further include an additional electrode layer laminated on the main electrode layer.

Nishiyama et al. teaches a boundary acoustic wave device in which the electrodes each include an additional electrode layer (Fig 1F and 1G, item 5) laminated on the main electrode layer (item 4A).

At the time of invention, it would have been obvious to a person of ordinary skill in the art to combine the additional electrode of Nishiyama et al. with the boundary acoustic wave device of Itakura et al. as modified by Taniguchi and Takayama et al. for the benefit of providing a protective film for the main electrode (Paragraph 160 of Nishiyama et al.).

22. With respect to claim 37, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 36. Itakura discloses that the solid layer includes a dielectric substance (Paragraph 97).

23. With respect to claim 38, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 37. Itakura et al. discloses that the dielectric substance includes a material primarily composed of SiO₂ (Paragraph 97).

24. With respect to claim 41, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 37. Itakura et al. discloses that the solid layer includes at least one material selected from the group consisting of Si, SiO₂, glass, silicon nitride, silicon carbide, ZnO, Ta₂O₅,

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titanate zirconate lead piezoelectric ceramic, aluminum nitride, Al_2O_3 , LiTaO_3 , and LiNbO_3 (Paragraph 97).

25. Claims 39 and 40 are rejected under 35 U.S.C. 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., Nishiyama, and Mishima et al. (US 20050099091).

26. With respect to claim 39, the combination of Itakura et al., Taniguchi, Takayama et al., and Nishiyama et al. discloses the boundary acoustic wave device according to claim 37.

None of Itakura et al., Taniguchi, Takayama et al., or Nishiyama et al. discloses that the solid layer includes a plurality of laminates, each of the plurality of laminates including a plurality of material layers.

Mishima et al. teaches a boundary acoustic wave device in which the solid layer includes a plurality of laminates, each of the plurality of laminates including a plurality of material layers (Fig 10, items 15 and 16).

At the time of invention, it would have been obvious to a person of ordinary skill in the art to combine the laminates solid layer of Mishima et al. with the boundary acoustic wave device of Itakura et al. as modified by Taniguchi, Takayama et al., and Nishiyama et al. for the benefit of preventing thermal damage during the manufacturing process (Paragraph 72 of Mishima et al.).

27. With respect to claim 40, the combination of Itakura et al., Taniguchi, Takayama et al., Nishiyama et al., and Mishima et al. discloses the boundary acoustic wave device according to claim 39. Mishima et al. discloses that the solid layer includes a layer

primarily composed of SiO₂ (item 15) laminated to a layer primarily composed of Si (item 16).

28. Claim 42 is rejected under 35 U.S.C. 103(a) as being unpatentable over Itakura et al. in view of Taniguchi, Takayama et al., and Kadota et al. (US 5260913).

29. With respect to claim 42, the combination of Itakura et al., Taniguchi, and Takayama et al. discloses the boundary acoustic wave device according to claim 29.

None of Itakura et al., Taniguchi, or Takayama et al. discloses expressly that the boundary acoustic wave elements each further includes a resin layer adhered to the solid layer.

Kadota et al. teaches a boundary acoustic wave device in which the boundary acoustic wave elements includes a resin layer (Fig 9, item 29) adhered to a solid layer (item 5).

At the time of invention, it would have been obvious to a person of ordinary skill in the art to combine the resin layer of Kadota et al. with the boundary acoustic wave device of Itakura et al. as modified by Taniguchi and Takayama et al. for the benefit of simplifying the manufacturing process of the device (column 6, lines 59-68 of Kadota et al.) and better protecting the device by placing the device in a packaging material.

Response to Arguments

30. Applicant's arguments, see amendments/arguments, filed 24 April 2008, with respect to the drawings have been fully considered and are persuasive. The objections to the drawings have been withdrawn.

31. Applicant's arguments filed 24 April 2008 have been fully considered but they are not persuasive. Applicant argues that all of Ikatura et al., Taniguchi, or Takayama et al. disclose surface acoustic wave devices, not boundary acoustic wave devices. However, at least Ikatura et al. discloses a boundary acoustic wave device. Applicant argues that Takayama et al. does not disclose "a thickness of the electrodes is set so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate". While Takayama et al. does not explicitly discuss the functional language "so that the acoustic velocity of an SH type boundary acoustic wave is lower than the acoustic velocity of a slow transverse wave propagating through the piezoelectric single crystal substrate", Takayama et al. does disclose the electrode thicknesses disclosed in the specification, and the above functional language would be inherent.

Conclusion

32. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of

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the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Derek J. Rosenau whose telephone number is (571)272-8932. The examiner can normally be reached on Monday thru Thursday 7:00-5:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Darren Schubert can be reached on 571-272-2044. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Derek J Rosenau
Examiner
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